



Docket No.: 52352-372

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Jeffrey A. SHIELDS, et al.

Serial No.: 09/498,336

Group Art Unit: 2812

Filed: February 04, 2000

Examiner: V. Perez

For: CF<sub>4</sub> + H<sub>2</sub>O PLASMA ASHING FOR REDUCTION OF CONTACT/VIA  
RESISTANCE

**REQUEST FOR RECONSIDERATION**

Commissioner for Patents  
Washington, DC 20231

Sir:

Reconsideration of the rejection under 35 U.S.C. §103 imposed in the Office  
Action dated July 17, 2001 is solicited in light of the following Remarks:

**REMARKS**

**Claims 1 through 20 were rejected under 35 U.S.C. §103 for obviousness  
predicated upon the acknowledged prior art in view of Solis.**

In the statement of the rejection, the Examiner concluded that one having ordinary skill in the art would have been motivated to modify the acknowledged prior art methodology by removing the photoresist layer employing an etch gas mixture comprising CF<sub>4</sub> and H<sub>2</sub>O in view of the teaching by Solis that such an etch gas mixture is very aggressive. This rejection is traversed.

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